Product Overview

FJP13009: High-Voltage Fast-Switching NPN Power Transistor

For complete documentation, see the data sheet.

The FJP13009 is a 700 V, 12 A NPN silicon epitaxial planar transistor. The FJP13009 is available with multiple hFE bin classes for ease of design use. The FJP13009 is designed for high speed switching applications which utilizes the industry standard TO-220 package offering flexibility in design and excellent power dissipation.

Features

- High-Voltage Capability
- High Switching Speed

Applications

- This product is general usage and suitable for many different applications.

Part Electrical Specifications

Product	Pricing ($/Unit)	Compliance	Status	Polarity	Type	$V_{CE(sat)}$ Max (V)	I_C Cont. (A)	V_{CEO} Min (V)	V_{CBO} (V)	V_{EBO} (V)	$V_{BE(sat)}$ (V)	$V_{BE(on)}$ (V)	h_{FE} Min	h_{FE} Max	f_T Min (MHz)	P_{TM} Max (W)	Package Type
FJP13009H2TU	0.46	Pb-free	Active	NPN	High Voltage Fast-Switching Power Transistor	3	12	400	700	9	1.6	-	15	40	4	100	TO-220-3
FJP13009TU	0.46	Pb-free	Active	NPN	High Voltage Fast-Switching Power Transistor	3	12	400	700	9	1.6	-	8	40	4	100	TO-220-3

For more information please contact your local sales support at www.onsemi.com.

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